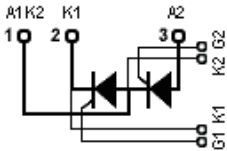


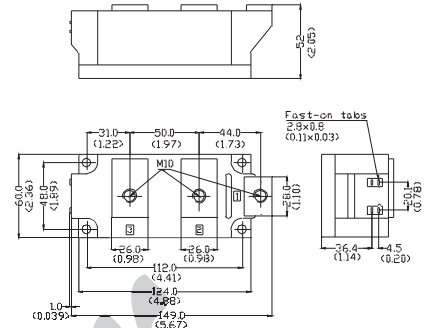
STT500GKxxBT

Thyristor-Thyristor Modules



Type	V_{RSM}	V_{RRM}
	V_{DSM}	V_{DRM}
	V	V
STT500GK08BT	900	800
STT500GK12BT	1300	1200
STT500GK14BT	1500	1400
STT500GK16BT	1700	1600
STT500GK18BT	1900	1800

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit
I_{TRMS} , I_{FRMS} I_{TAVM} , I_{FAVM}	$T_{VJ}=T_{VJM}$ $T_C=85^{\circ}C$; 180° sine	785 500	A
I_{TSM} , I_{FSM}	$T_{VJ}=45^{\circ}C$ $V_R=0$ t=10ms (50Hz), sine t=8.3ms (60Hz), sine	16000 18000	A
	$T_{VJ}=T_{VJM}$ $V_R=0$ t=10ms(50Hz), sine t=8.3ms(60Hz), sine	13000 14400	
i^2dt	$T_{VJ}=45^{\circ}C$ $V_R=0$ t=10ms (50Hz), sine t=8.3ms (60Hz), sine	1125000 1062000	A^2s
	$T_{VJ}=T_{VJM}$ $V_R=0$ t=10ms(50Hz), sine t=8.3ms(60Hz), sine	845000 813000	
$(di/dt)_{cr}$	$T_{VJ}=T_{VJM}$ f=50Hz, $t_p=200\mu s$ $V_D=2/3V_{DRM}$ $I_G=1A$ $di_G/dt=1A/\mu s$ repetitive, $I_T=960A$	100	A/ μs
	non repetitive, $I_T=I_{TAVM}$	500	
$(dv/dt)_{cr}$	$T_{VJ}=T_{VJM}$; $R_{GK}=\infty$; method 1 (linear voltage rise) $V_{DR}=2/3V_{DRM}$	1000	V/ μs
P_{GM}	$T_{VJ}=T_{VJM}$ $I_T=I_{TAVM}$ $t_p=30\mu s$ $t_p=500\mu s$	120 60	W
P_{GAV}		20	W
V_{RGM}		10	V
T_{VJ} T_{VJM} T_{stg}		-40...+140 140 -40...+125	$^{\circ}C$
V_{ISOL}	50/60Hz, RMS $I_{ISOL}\leq 1mA$ t=1min t=1s	3000 3600	V~
M_d	Mounting torque (M6) Terminal connection torque (M8)	4.5-7/40-60 11-13/97-115	Nm/lb.in.
Weight	Typical	1380	g

STT500GKXXBT

Thyristor-Thyristor Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_{RRM}	$T_{VJ}=T_{VJM}; V_R=V_{RRM}$	30	mA
V_{TM}	$I_{TM}=1500A; T_{VJ}=25^{\circ}C$	1.65	V
V_{TO}	For power-loss calculations only ($T_{VJ}=T_{VJM}$)	0.8	V
r_T		0.38	m
V_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	2 3	V
I_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	300 400	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.25	V
I_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	10	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=30\mu s; V_D=6V$ $I_G=1A; di_G/dt=1A/\mu s$	400	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	300	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=1A; di_G/dt=1A/\mu s$	2	us
t_q	$T_{VJ}=T_{VJM}; I_T=500A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=50V/\mu s; V_D=2/3V_{DRM}$ typ.	350	us
R_{thJC}	DC current	0.072	K/W
R_{thJK}	DC current	0.096	K/W
d_s	Creeping distance on surface	12.7	mm
d_A	Creepage distance in air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Pressure Contact Technology
- * BusBar Terminal
- * Isolation voltage 3600 V~
- * UL file NO.310749
- * RoHS compliant

APPLICATIONS

- * Motor control, softstarter
- * Power converter
- * Heat and temperature control for industrial furnaces and chemical processes
- * Lighting control
- * Solid state switches

ADVANTAGES

- * Simple mounting
- * Improved temperature and power cycling
- * Reduced protection circuits



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Thyristor-Thyristor Modules

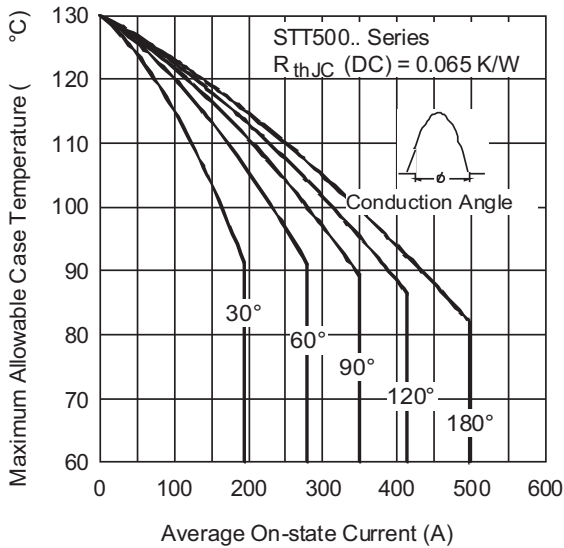


Fig. 1 - Current Ratings Characteristics

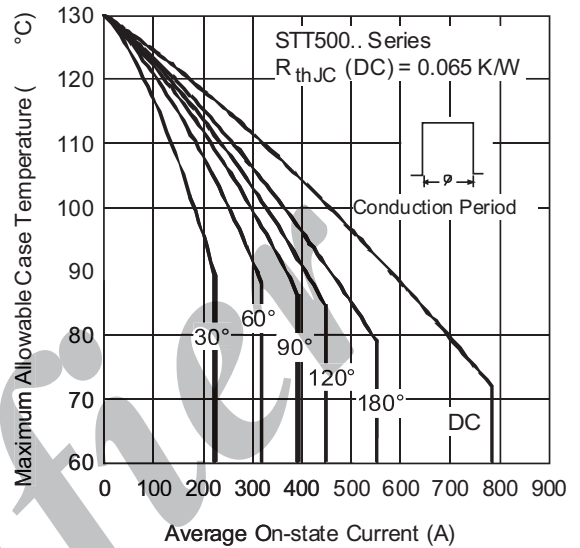


Fig. 2 - Current Ratings Characteristics

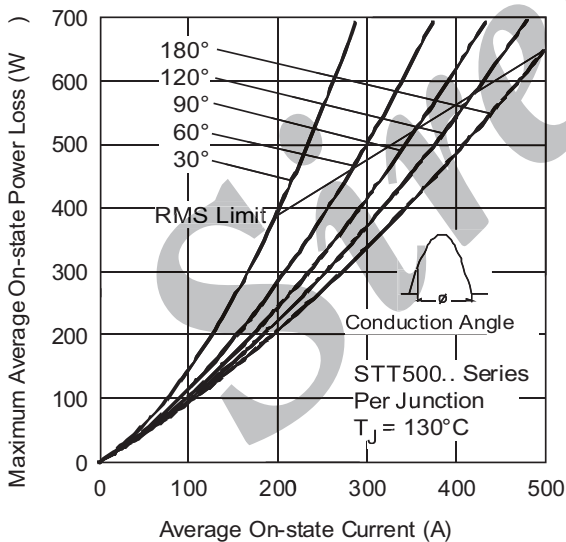


Fig. 3 - On-state Power Loss Characteristics

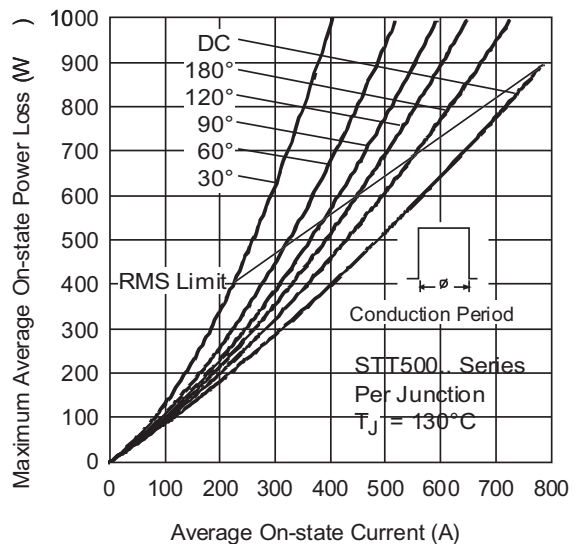


Fig. 4 - On-state Power Loss Characteristics

STT500GKXXBT

Thyristor-Thyristor Modules

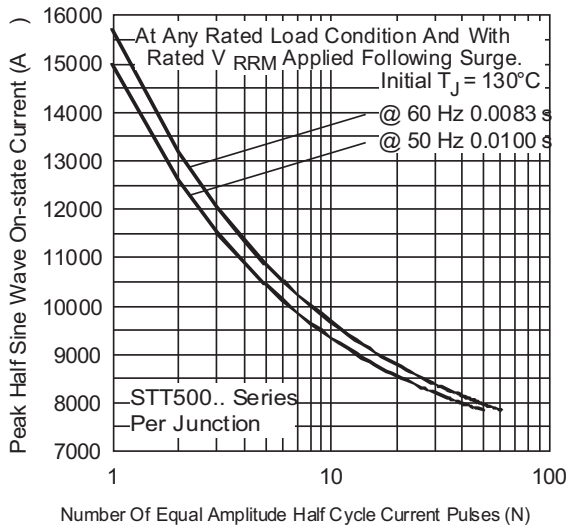


Fig. 5 - Maximum Non-Repetitive Surge Current

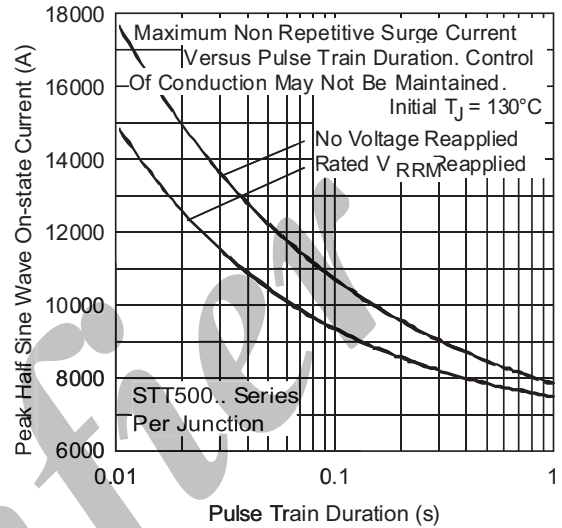


Fig. 6 - Maximum Non-Repetitive Surge Current

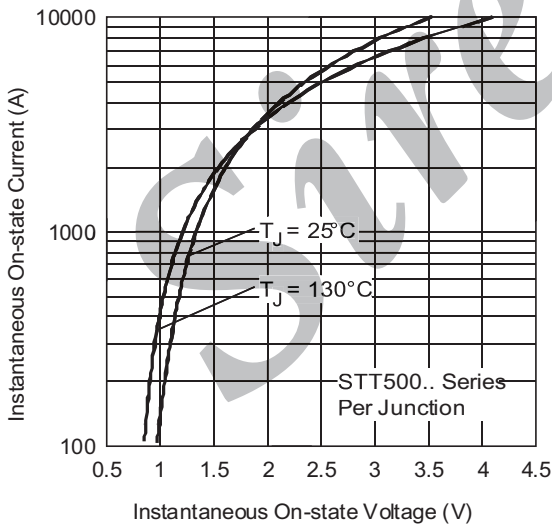


Fig. 7 - On-state Voltage Drop Characteristics

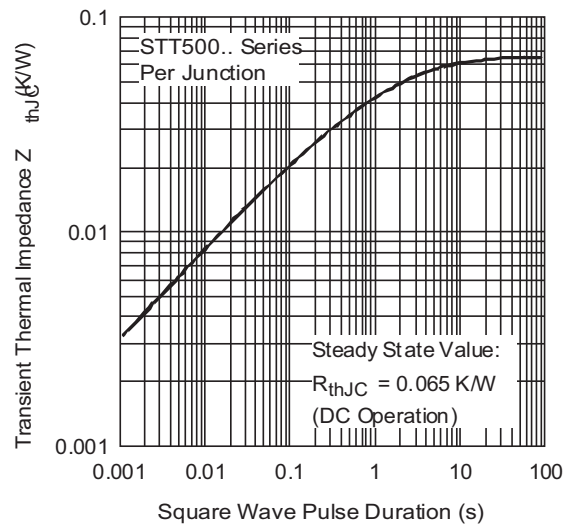


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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Thyristor-Thyristor Modules

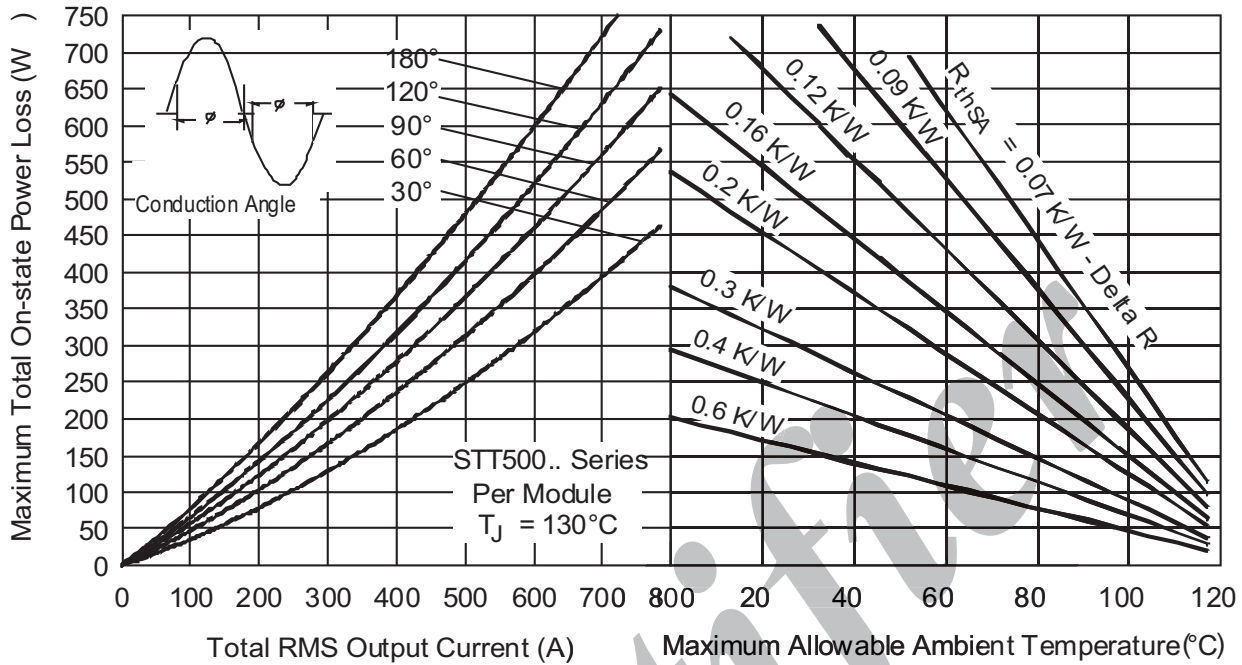


Fig. 9 - On-state Power Loss Characteristics

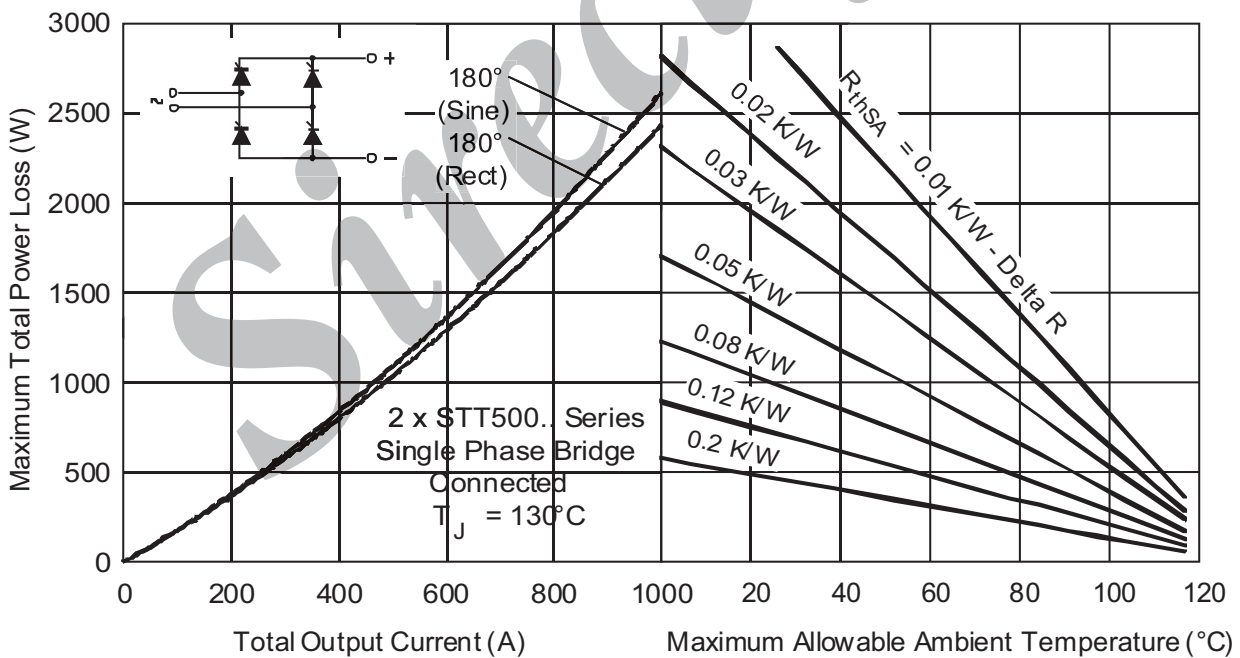


Fig. 10 - On-state Power Loss Characteristics

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Thyristor-Thyristor Modules

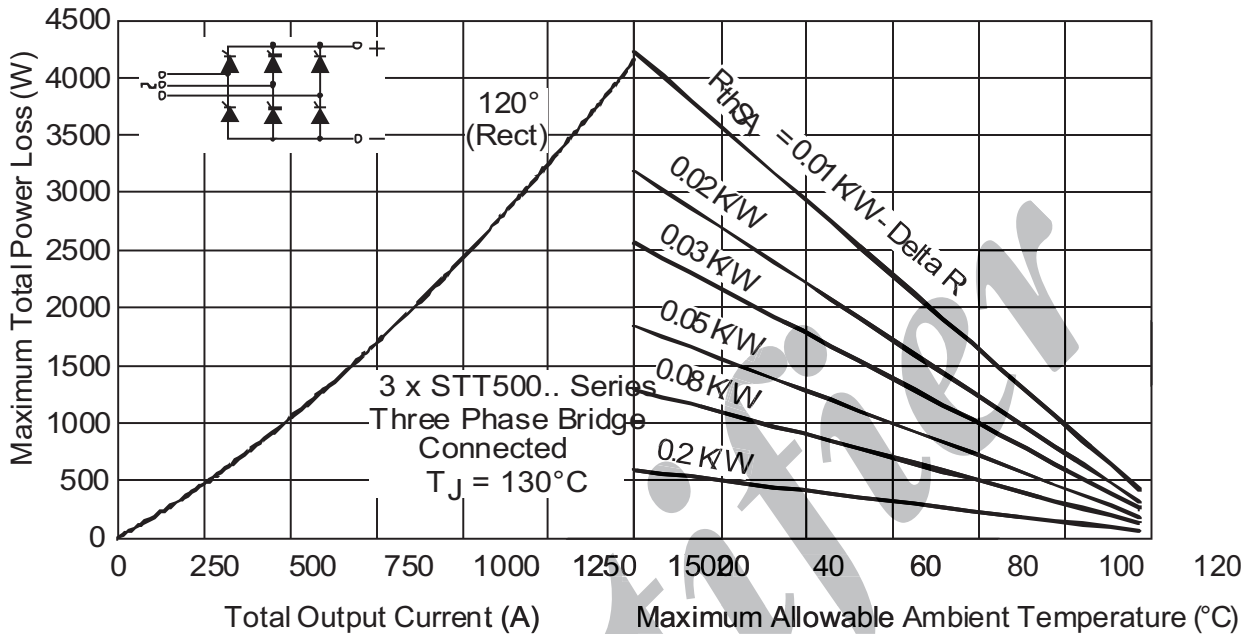


Fig. 11 - On-state Power Loss Characteristics

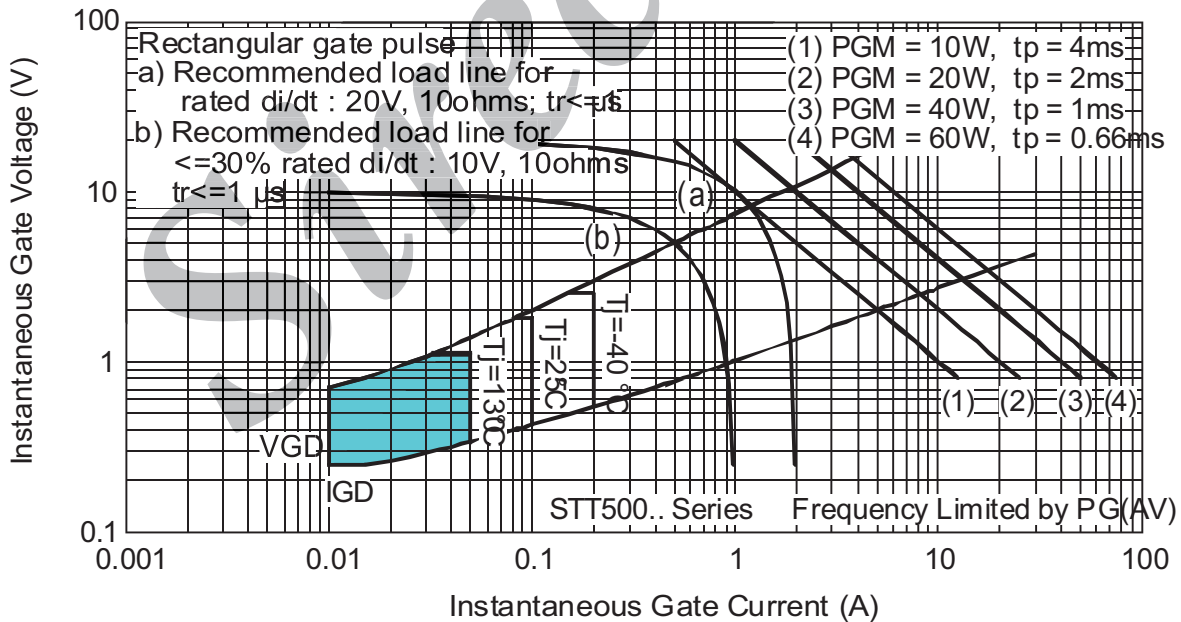


Fig. 12 - Gate Characteristics